

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-9 (canceled).

Claim 10 (original): A surface acoustic wave apparatus, comprising:

a piezoelectric substrate;

at least one electrode for a surface acoustic wave element disposed on the piezoelectric substrate;

an electrode pad disposed on the piezoelectric substrate and arranged to be joined with a bump during a bump bonding process performed by a flip chip bonding system; and

a wiring electrode for electrically connecting the electrode pad and the electrode for surface acoustic wave element;

wherein the electrode pad includes a first electrode layer disposed on the piezoelectric substrate and a second electrode layer laminated on the first electrode layer, the first electrode layer including an etched metal film, and the at least one electrode for the surface acoustic wave element including a material formed by a lift-off process.

Claim 11 (original): The surface acoustic wave apparatus according to Claim 10,

wherein the wiring electrode and the second electrode layer are integral with each other and include a common metal film.

Claim 12 (original): The surface acoustic wave apparatus according to Claim 10, further comprising an adhesive layer defining a substrate for the wiring electrode and the second electrode layer, wherein the wiring electrode and the second electrode layer are made of one of an Al and an Al alloy, and the adhesive layer is made one of a metal and an alloy having an adhesion to the first electrode layer that is higher than that of the Al and the Al alloy.

Claim 13 (original): A surface acoustic wave apparatus, comprising:
a piezoelectric substrate;
at least one electrode for a surface acoustic wave element disposed on the piezoelectric substrate;
an electrode pad disposed on the piezoelectric substrate and arranged to be joined with a bump during a bump bonding process performed by a flip chip bonding system; and
a wiring electrode for electrically connecting the electrode pad and the electrode for the surface acoustic wave element, wherein:
the electrode pad includes a first electrode layer disposed on the piezoelectric substrate and a second electrode layer laminated on the first electrode layer;
the second electrode layer and the wiring electrode are integral with each and include the same conductive film; and

end surfaces of joint portions, to be electrically connected with the wiring electrodes, of the first electrode layer and the electrode for the surface acoustic wave element are arranged to have a stepwise configuration.

Claim 14 (original): The surface acoustic wave apparatus according to Claim 10, wherein each of the electrode for the surface acoustic wave element and the first electrode layer of the electrode pad includes at least two end surfaces of the joint portion.

Claim 15 (original): The surface acoustic wave apparatus according to Claim 13, wherein each of the electrode for the surface acoustic wave element and the first electrode layer of the electrode pad includes at least two end surfaces of the joint portion.

Claim 16 (original): A surface acoustic wave apparatus, comprising:
a piezoelectric substrate;
at least one electrode for a surface acoustic wave element disposed on the piezoelectric substrate;
an electrode pad disposed on the piezoelectric substrate and arranged to be joined with a bump during a bump bonding process performed by a flip chip bonding system; and
a wiring electrode for electrically connecting the electrode pad and the electrode for the surface acoustic wave element, wherein:

the electrode pad includes a first electrode layer disposed on the piezoelectric substrate and a second electrode layer laminated on the first electrode layer;

the second electrode layer and the electrode for the surface acoustic wave element are integral with each other and include a common conductive film; and

the electrode for the surface acoustic wave element and the first electrode layer of the electrode pad, to be connected with the electrode for the surface acoustic wave element, are arranged in contact with each other.

Claim 17 (original): The surface acoustic wave apparatus according to Claim 10, wherein a particle size of a conductive particle in the conductive film constituting the second electrode layer and the wiring electrode is smaller than a particle diameter of a conductive particle in one of the electrode for the surface acoustic wave element and the first electrode layer of the electrode pad, which has a smaller film thickness.

Claim 18 (original): The surface acoustic wave apparatus according to Claim 13, wherein a particle size of a conductive particle in the conductive film constituting the second electrode layer and the wiring electrode is smaller than a particle diameter of a conductive particle in one of the electrode for the surface acoustic wave element and the first electrode layer of the electrode pad, which has a smaller film thickness.

Claim 19 (original): The surface acoustic wave apparatus according to Claim 15, wherein a particle size of a conductive particle in the conductive film constituting the second electrode layer and the wiring electrode is smaller than a particle diameter of a

conductive particle in one of the electrode for the surface acoustic wave element and the first electrode layer of the electrode pad, which has a smaller film thickness.

Claim 20 (original): The surface acoustic wave apparatus according to Claim 10, wherein an electrode for a second surface acoustic wave element that is different from the electrode for the surface acoustic wave element is disposed on the piezoelectric substrate, and the electrode for the second surface acoustic wave element includes an etched metal film.

Claim 21 (original): The surface acoustic wave apparatus according to Claim 13, wherein an electrode for a second surface acoustic wave element that is different from the electrode for the surface acoustic wave element is disposed on the piezoelectric substrate, and the electrode for the second surface acoustic wave element includes an etched metal film.

Claim 22 (original): The surface acoustic wave apparatus according to Claim 15, wherein an electrode for a second surface acoustic wave element that is different from the electrode for the surface acoustic wave element is disposed on the piezoelectric substrate, and the electrode for the second surface acoustic wave element includes an etched metal film.